trinno
Technology Leader in Power Semiconductor

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Technology Leader in Power Semiconductor trinno

Power Semiconductor SELECTION GUIDE

IGBT / DIODE / MOSFET / SiC

Company Introduction

As an innovator of Power Semiconductor Devices, TRinno has been providing highly efficient and optimum power solutions relying on leading edge technologies for valuable customers in China, Korea, Taiwan, Germany, US and India since 2008.

Including IGBTs, Super junction MOSFETs, TRinno is committed to development of SiC technology to meet increasing demands of customers.

With best power solutions, TRinno will be an indispensible partner for your business.

TRinno Technology

Ordering Information

Discrete

T G AN 40 N 60 F2 DS
A B C D E F G H

A TRinno Technology

B Product Family
M : Planar MOSFET / S : Super Junction MOSFET / MC : SiC MOSFET
G : IGBT / D : DIODE / DC : SiC DIODE / N : Trench MOSFET

C Package Type
B / D / U : D2-PAK / D-PAK / I-PAK
P / PF : TO-220 / TO-220F
A / AN / AF / H / L : TO-3P / TO-3PN / TO-3PF / TO-247 / TO-264

D Current Rating / On-resistance($R_{DS(on),max.}$)
Superjunction MOSFET : maximum on-resistance (mΩ)
Others : Current Rating (A)

E Channel Polarity / DIODE Speed
MOSFET/IGBT : N (N-type), P (P-Type), S (Reverse conducting IGBT), R (On-resistance)
DIODE : A (Low V_f), B (Standard) , C(Low Qrr)

F Voltage Rating
absolute voltage rating divided by '10'

G Generation / Technology
MOSFET : No suffix (1st gen.), A (2nd gen.)
IGBT : N (Non Punch Through), F (Field Stop), P (Punch Through)
F2 / F3 / Fx (Field Stop: 2nd / 3rd / ... Generation)

H Option
MOSFET : Z (G-S Zener Diode), S (Fast Recovery)
IGBT : C (SiC Diode), D (Anti-parallel Diode), L (Low Vce,sat),
R (Short Circuit Rated), S (Fast Switching), W (for Welder)
DIODE : DN (Common Cathode), DP (Common Anode)
PACKAGE : G (Halogen Free)

Module

T PM 100 GB 120 R N
A B C D E F G

A TRinno Technology

B Power Module
PM (Power Module), PIM (Power Integration Module)

C Current Rating

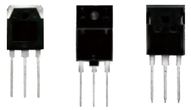
D Topology
GB (IGBT Bridge type), R (Bridge+C/B+3-phase)

E Voltage Rating (divided by '10')

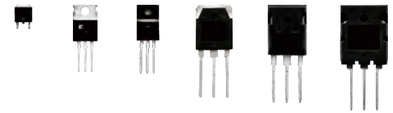
F Package Type
R (34mm), K (62mm), M3 (EconoPower3), W2 (EasyPower2)

G IGBT Technology
N (NPT), F (FS)

IGBT Discrete



TO-3PN TO-3PF TO-247



D-PAK TO-220 TO-220F TO-3PN TO-247 TO-264

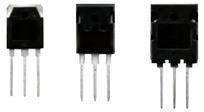
V_{CES} [V]	Part Number	I_C @25℃ [A]	I_C @100℃ [A]	$V_{CE(SAT),max}$ @25℃ [V]	$V_{CE(SAT),typ}$ @25℃ [V]	$E_{OFF,typ}$ @25℃ [mJ]	Anti-Parallel Diode	Package	Feature/Status
600	TGAN20N60FDR*	40	20	2.0	1.5	0.44	Yes	TO-3PN	Short Circuit Rated
	TGAN30N60FDR	60	30	2.0	1.5	0.66	Yes		Short Circuit Rated
	TGAN40N60FD	80	40	2.3	1.8	0.54	Yes		
	TGAN40N60F2D	80	40	2.2	1.7	0.49	Yes		
	TGAN40N60F2DS	80	40	2.4	2.0	0.53	Yes		High Speed Switching
	TGAN60N60FD	120	60	2.3	1.8	1.53	Yes		
	TGAN60N60F2D	120	60	2.2	1.7	1.70	Yes		
	TGAN60N60F2DS	120	60	2.2	1.8	1.52	Yes		High Speed Switching
	TGAN80N60F2DS	160	80	2.2	1.8	2.22	Yes		High Speed Switching
	TGAF40N60F2D	80	40	2.2	1.7	0.53	Yes	TO-3PF	
	TGH20N60FDR*	40	20	2.0	1.5	0.4	Yes	TO-247*	Short Circuit Rated
	TGH30N60FDR*	60	30	2.0	1.5	0.66	Yes		Short Circuit Rated
	TGH40N60F2D*	80	40	2.2	1.7	0.49	Yes		
	TGH60N60F2DS*	120	60	2.2	1.8	1.52	Yes		High Speed Switching
	TGH80N60F2DS*	160	80	2.2	1.8	2.22	Yes		High Speed Switching

* Under Development

V_{CES} [V]	Part Number	I_C @25℃ [A]	I_C @100℃ [A]	$V_{CE(SAT),max}$ @25℃ [V]	$V_{CE(SAT),typ}$ @25℃ [V]	$E_{OFF,typ}$ @25℃ [mJ]	Anti-Parallel Diode	Package	Feature/Status
600	TGL80N60F2DS*	160	80	2.2	1.8	2.22	Yes	TO-264	High Speed Switching
	TGP5N60FDR*	10	5	2.0	1.5	TBD	Yes	TO-220	Short Circuit Rated
	TGP10N60FDR*	20	10	2.0	1.5	TBD	Yes		Short Circuit Rated
	TGP15N60FDR	30	15	2.0	1.5	0.21	Yes		Short Circuit Rated
	TGP20N60FDR	40	20	2.0	1.5	0.39	Yes		Short Circuit Rated
	TGPF15N60FDR	30	15	2.0	1.5	0.21	Yes	TO-220F	Short Circuit Rated
	TGPF20N60FDR	40	20	2.0	1.5	0.39	Yes		Short Circuit Rated
	TGD5N60FDR*	10	5	2.0	1.5	TBD	Yes	D-PAK	Short Circuit Rated
	TGD10N60FDR*	20	10	2.0	1.5	TBD	Yes		Short Circuit Rated
	TGD15N60FDR*	30	15	2.0	1.5	TBD	Yes		Short Circuit Rated
650	TGAN40N65F2DS*	80	40	2.2	1.8	TBD	Yes	TO-3PN	High speed switching
	TGAN60N65F2DS*	120	60	2.2	1.8	TBD	Yes		High speed switching
	TGAN80N65F2DS	160	80	2.2	1.8	2.60	Yes		High speed switching
	TGH40N65F2DS*	80	40	2.2	1.8	TBD	Yes	TO-247*	High speed switching
	TGH60N65F2DS*	120	60	2.2	1.8	TBD	Yes		High speed switching

* Under Development

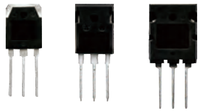
IGBT Discrete



TO-3PN TO-247 TO-264

V_{CES} [V]	Part Number	I_C @25℃ [A]	I_C @100℃ [A]	$V_{CE(SAT),max}$ @25℃ [V]	$V_{CE(SAT),typ}$ @25℃ [V]	$E_{OFF,typ}$ @25℃ [mJ]	Anti-Parallel Diode	Package	Feature/Status
650	TGH80N65F2DS*	160	80	2.2	1.8	2.60	Yes	TO-247*	High speed switching
900	TGAN40N90FD	80	40	2.5	2.0	1.10	Yes	TO-3PN	
	TGAN40S90FD*	80	40	TBD	TBD	TBD	Yes		Reverse Conducting IGBT
1000	TGL60N100ND1	60	42	2.9	2.3	6.30	Yes	TO-264	
1100	TGAN40N110FD	80	40	2.5	2.0	1.20	Yes	TO-3PN	
1200	TGAN15N120FDR	30	15	1.8	1.5	0.74	Yes	TO-3PN	Short Circuit Rated
	TGAN15N120ND	30	15	2.5	1.9	0.53	Yes		
	TGAN20N120FDV	40	20	2.3	2.0	0.48	Yes		
	TGAN25N120FDR	50	25	2.5	2.0	0.92	Yes		Short Circuit Rated
	TGAN25N120ND	50	25	2.5	1.9	0.87	Yes		
	TGAN30N120FD	60	30	2.5	2.0	0.85	Yes		
	TGAN40N120FD	80	40	2.6	2.0	1.10	Yes		
	TGAN40N120F2D	80	40	2.32	1.82	1.35	Yes		
	TGAN40N120F2DW	80	40	2.4	2.00	1.40	Yes		
	TGAN40N120FDR	80	40	2.5	2.0	1.30	Yes		Short Circuit Rated

* Under Development

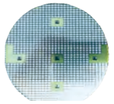


TO-3PN TO-247 TO-264

V_{CES} [V]	Part Number	I_C @25℃ [A]	I_C @100℃ [A]	$V_{CE(SAT),max}$ @25℃ [V]	$V_{CE(SAT),typ}$ @25℃ [V]	$E_{OFF,typ}$ @25℃ [mJ]	Anti-Parallel Diode	Package	Feature/Status
1200	TGH15N120FDR*	30	15	1.8	1.5	0.74	Yes	TO-247*	Short Circuit Rated
	TGH25N120FDR*	50	25	2.5	2.0	0.92	Yes		Short Circuit Rated
	TGH30N120FD*	60	30	2.5	2.0	0.85	Yes		
	TGH40N120FD*	80	40	2.6	2.0	1.10	Yes		
	TGH40N120FDR*	80	40	2.5	2.0	1.30	Yes		Short Circuit Rated
	TGL40N120FD	80	40	2.6	2.0	1.10	Yes	TO-264	
	TGL60N120FDR*	120	60	2.5	2.0	TBD	Yes		Short Circuit Rated
1350	TGAN15S135FD	30	15	2.35	1.95	0.54	Yes	TO-3PN	Reverse Conducting IGBT
	TGAN20N135FD	40	20	2.3	1.8	0.76	Yes		
	TGAN20S135FD	40	20	2.15	1.75	1.32	Yes		Reverse Conducting IGBT
	TGAN30N135FD1	60	30	2.4	1.9	1.18	Yes		
	TGAN30S135FD*	60	30	2.15	1.75	TBD	Yes		Reverse Conducting IGBT

* Under Development

IGBT Wafer / Die



Wafer

V_{CES} [V]	Part Number	I_C @100℃ [A]	$V_{CE(SAT),typ}$ @25℃ [V]	$V_{CE(SAT),max}$ @25℃ [V]	$E_{OFF,typ}$ @25℃ [mJ]	$V_{ge(TH),tye}$ @25℃ [V]	Package	Feature/Status
600	TG75N60NWA	75	2.1	2.6	1.6	6.5	Wafer	Gen.2 NPT Trench IGBT
	TG100N60NWA	100	2.1	2.6	2.1	6.5		
	TG150N60NWA	150	2.1	2.6	3.1	6.5		
	TG200N60NWA	200	2.1	2.6	4.2	6.5		
1200	TG100N120FWX*	100	TBD	TBD	TBD	TBD		FS Trench IGBT

* Under Development

IGBT Module

34mm Module

62mm Module

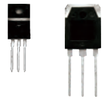
EconoPower3

EasyPower2

V_{CES} [V]	Part Number	I_C @100℃ [A]	$V_{CE(SAT),typ}$ @25℃ [V]	$V_{CE(SAT),max}$ @25℃ [V]	$V_{F(typ)}$ @25℃ [V]	$V_{F(max)}$ @25℃ [V]	Package	Feature/Status
1200	TPM75GB120RN	75	2.5	2.9	1.9	2.3	34mm 2-Pack	Half Bridge
	TPM100GB120RN	100	2.5	2.9	1.9	2.3		
	TPM150GB120RN	150	2.5	2.9	1.9	2.3		
	TPM150GB120KN	150	2.5	2.9	1.9	2.3	62mm 2-Pack	
	TPM200GB120KN	200	2.5	2.9	1.9	2.3		
	TPM300GB120KN	300	2.5	2.9	1.9	2.3		
	TPM300GB120M3F*	300	TBD	TBD	TBD	TBD	EconoPower3*	
	TPM450GB120M3F*	450	TBD	TBD	TBD	TBD		
	TPIM25R12W2F*	25	TBD	TBD	TBD	TBD	EasyPower2*	Bridge+C/B+Inverter
	TPIM35R12W2F*	35	TBD	TBD	TBD	TBD		

* Under Development

DIODE



TO-220F TO-3PN

V_{RRM} [V]	Part Number	$I_{F(AV)}$ [A]	I_{FSM} [A]	$V_{F(max)}$ @25℃ [V]	$V_{F(typ)}$ @25℃ [V]	$t_{rr(typ)}$ @25℃[ns]	Package	Feature/Status
600 / 650*	TDPF10B60	10	100	2.10	1.60	58	TO-220F 2L	
	TDPF20B60	20	200	2.10	1.60	56		
	TDPF30B60	30	300	2.00	1.50	85		
	TDAN30B60*	30	300	2.10	1.60	TBD	TO-3PN 2/3L	
	TDAN60B60DN	60	600	2.00	1.50	85		Common Cathode Type
1200	TDAN50B120DN*	50	TBD	2.20	TBD	TBD	TO-3PN 3L	Common Cathode Type
650	TDCAN30B65*	30	TBD	1.70	TBD	TBD	TO-3PN 2L	SiC DIODE
1200	TDCAN30B120*	30	TBD	1.90	TBD	TBD		SiC DIODE

* Under Development

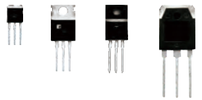
Trench MOSFET

TO-247

V_{DSS} [V]	Part Number	I_D @25℃ [A]	$R_{DS(on),max}$ @25℃ [Ω]	$V_{GS(th),typ}$ [V]	Polarity	Package	Feature/Status
40	TNH200N04	200.0	0.002	3.0	N	TO-247	AEC-Q101 qualified
80	TNH180N08*	180.0	0.0035	3.0	N		AEC-Q101 Ready
100	TNH150N10*	150.0	0.005	3.0	N		AEC-Q101 Ready

* Under Development

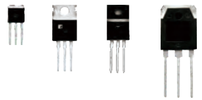
Planar MOSFET



I-PAK TO-220 TO-220F TO-3PN

V_{DSS} [V]	Part Number	I_D @25℃ [A]	$R_{DS(on),max}$ @25℃ [Ω]	$V_{GS(th),typ}$ [V]	Polarity	Package	Feature/Status
200	TMPF630Z	9.0	0.40	4.0	N	TO-220F	Built-in G-S Zener Diode
	TMPF18N20Z	18.0	0.17	4.0	N		Built-in G-S Zener Diode
	TMP630Z	9.0	0.40	4.0	N	TO-220	Built-in G-S Zener Diode
	TMP18N20Z	18.0	0.17	4.0	N		Built-in G-S Zener Diode
	TMU630Z	9.0	0.40	4.0	N	I-PAK	Built-in G-S Zener Diode
	TMU18N20Z	18.0	0.17	4.0	N		Built-in G-S Zener Diode
250	TMPF8N25Z	8.0	0.60	4.0	N	TO-220F	Built-in G-S Zener Diode
	TMPF16N25Z	16.0	0.24	4.0	N		Built-in G-S Zener Diode
	TMP8N25Z	8.0	0.60	4.0	N	TO-220	Built-in G-S Zener Diode
	TMP16N25Z	16.0	0.24	4.0	N		Built-in G-S Zener Diode
	TMU8N25Z	8.0	0.60	4.0	N	I-PAK	Built-in G-S Zener Diode
	TMU16N25Z	16.0	0.24	4.0	N		Built-in G-S Zener Diode
400	TMU3N40Z	2.0	3.40	3.0	N	I-PAK	Built-in G-S Zener Diode
	TMU5N40Z	3.4	1.60	3.0	N		Built-in G-S Zener Diode
500	TMAN15N50	14.2	0.4	3.0	N	TO-3PN	
	TMAN20N50	20.0	0.3	3.0	N		
	TMAN23N50	23.0	0.2	3.0	N		
	TMPF3N50Z	2.5	2.8	3.0	N	TO-220F	Built-in G-S Zener Diode
	TMPF830AZ	4.5	1.5	4.0	N		Built-in G-S Zener Diode
	TMPF8N50Z	8.0	0.9	4.0	N		Built-in G-S Zener Diode

* Under Development



I-PAK TO-220 TO-220F TO-3PN

V_{DSS} [V]	Part Number	I_D @25℃ [A]	$R_{DS(on),max}$ @25℃ [Ω]	$V_{GS(th),typ}$ [V]	Polarity	Package	Feature/Status
500	TMPF9N50	9.0	0.9	3.0	N	TO-220F	
	TMPF11N50	11.0	0.7	3.0	N		
	TMPF13N50A	13.0	0.5	4.0	N		
	TMPF15N50	14.0	0.4	3.0	N		
	TMPF20N50	18.0	0.3	3.0	N		
	TMP3N50AZ	2.5	2.8	4.0	N	TO-220	Built-in G-S Zener Diode
	TMP3N50Z	2.5	2.8	3.0	N		Built-in G-S Zener Diode
	TMP830AZ	4.5	1.5	4.0	N		Built-in G-S Zener Diode
	TMP8N50Z	8.0	0.9	4.0	N		Built-in G-S Zener Diode
	TMP9N50	9.0	0.9	3.0	N		
	TMP11N50	11.0	0.7	3.0	N		
	TMP13N50A	13.0	0.5	4.0	N		
	TMP15N50	14.0	0.4	3.0	N		
	TMP20N50	18.0	0.3	3.0	N		
	TMU3N50Z	2.5	2.8	3.0	N	I-PAK	Built-in G-S Zener Diode
	TMU830AZ	4.5	1.5	4.0	N		Built-in G-S Zener Diode
600	TMAN16N60	16.0	0.5	3.0	N	TO-3PN	
	TMAN20N60A	20.0	0.3	4.0	N		
	TMPF2N60AZ	2.0	4.0	4.0	N	TO-220F	Built-in G-S Zener Diode
	TMPF4N60AZ	4.0	2.5	4.0	N		Built-in G-S Zener Diode

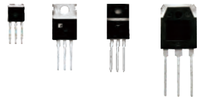
* Under Development

Planar MOSFET

I-PAK TO-220 TO-220F

V_{DSS} [V]	Part Number	I_D @25℃ [A]	$R_{DS(on),max}$ @25℃ [Ω]	$V_{GS(th),typ}$ [V]	Polarity	Package	Feature/Status
600	TMPF5N60AZ	4.2	2.1	4.0	N	TO-220F	Built-in G-S Zener Diode
	TMPF8N60AZ	7.5	1.2	4.0	N		Built-in G-S Zener Diode
	TMPF9N60	9.0	1.0	3.0	N		
	TMPF10N60A	10.0	0.7	4.0	N		
	TMPF12N60A	12.0	0.7	4.0	N		
	TMPF16N60	16.0	0.5	3.0	N		
	TMP2N60AZ	2.0	4.0	4.0	N	TO-220	Built-in G-S Zener Diode
	TMP4N60AZ	4.0	2.5	4.0	N		Built-in G-S Zener Diode
	TMP5N60AZ	4.2	2.1	4.0	N		Built-in G-S Zener Diode
	TMP8N60AZ	7.5	1.2	4.0	N		Built-in G-S Zener Diode
	TMP9N60	9.0	1.0	3.0	N		
	TMP10N60A	10.0	0.7	4.0	N		
	TMP12N60A	12.0	0.7	4.0	N		
	TMP16N60	16.0	0.5	3.0	N		
	TMU2N60AZ	2.0	4.0	4.0	N	I-PAK	Built-in G-S Zener Diode
	TMU4N60AZ	4.0	2.5	4.0	N		Built-in G-S Zener Diode
	TMU5N60AZ	4.2	2.1	4.0	N		Built-in G-S Zener Diode
650	TMPF2N65AZ	1.8	4.6	4.0	N	TO-220F	Built-in G-S Zener Diode
	TMPF4N65AZ	4.0	2.4	4.0	N		Built-in G-S Zener Diode
	TMPF7N65AZ	6.5	1.4	4.0	N		Built-in G-S Zener Diode

* Under Development

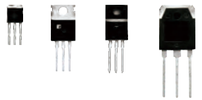


I-PAK TO-220 TO-220F TO-3PN

V_{DSS} [V]	Part Number	I_D @25℃ [A]	$R_{DS(on),max}$ @25℃ [Ω]	$V_{GS(th),typ}$ [V]	Polarity	Package	Feature/Status
650	TMPF10N65A	9.5	0.8	4.0	N	TO-220F	
	TMP2N65AZ	1.8	4.6	4.0	N	TO-220	Built-in G-S Zener Diode
	TMP4N65AZ	4.0	2.4	4.0	N		Built-in G-S Zener Diode
	TMP7N65AZ	6.5	1.4	4.0	N		Built-in G-S Zener Diode
	TMP10N65A	9.5	0.8	4.0	N		
	TMU2N65AZ	1.8	4.6	4.0	N	I-PAK	Built-in G-S Zener Diode
	TMU4N65AZ	4.0	2.4	4.0	N		Built-in G-S Zener Diode
700	TMPF6N70	5.0	1.7	3.0	N	TO-220F	
	TMPF9N70	9.0	1.1	3.0	N		
	TMP6N70	5.0	1.7	3.0	N	TO-220	
	TMP9N70	9.0	1.1	3.0	N		
800	TMAN10N80	10.0	1.1	3.0	N	TO-3PN	
	TMAN12N80AZ	12.0	0.7	4.0	N		Built-in G-S Zener Diode
	TMPF3N80	3.0	4.2	3.0	N	TO-220F	
	TMPF4N80	4.0	3.0	3.0	N		
	TMPF7N80A	7.0	1.9	3.0	N		
	TMPF8N80	8.0	1.4	3.0	N		
	TMPF10N80	9.5	1.1	3.0	N		
	TMP3N80	3.0	4.2	3.0	N	TO-220	
	TMP4N80	4.0	3.0	3.0	N		

* Under Development

Planar MOSFET



I-PAK TO-220 TO-220F TO-3PN

V_{DSS} [V]	Part Number	I_D @25℃ [A]	$R_{DS(on),max}$ @25℃ [Ω]	$V_{GS(th),typ}$ [V]	Polarity	Package	Feature/Status
800	TMP7N80A	7.0	1.9	3.0	N	TO-220	
	TMP8N80	8.0	1.4	3.0	N		
	TMP10N80	9.5	1.1	3.0	N		
	TMU3N80	3.0	4.2	3.0	N	I-PAK	
900	TMAN7N90	7.2	1.9	3.0	N	TO-3PN	
	TMAN9N90AZ	9.0	1.4	3.0	N		Built-in G-S Zener Diode
	TMAN11N90AZ	11.0	0.9	4.0	N		Built-in G-S Zener Diode
	TMPF3N90	2.5	5.1	3.0	N	TO-220F	
	TMPF4N90	4.0	4.0	3.0	N		
	TMPF7N90	7.0	1.9	3.0	N		
	TMP3N90	2.5	5.1	3.0	N	TO-220	
	TMP4N90	4.0	4.0	3.0	N		
	TMP7N90	7.0	1.9	3.0	N		
	TMU3N90	2.5	5.1	3.0	N	I-PAK	
1200	TMCAN400R120*	10.0	0.4	3.0	N	TO-3PN	SiC MOSFET
	TMCAN150R120*	30.0	0.15	3.0	N		SiC MOSFET

* Under Development

Super Junction MOSFET

TO-3PN

V_{DSS} [V]	Part Number	I_D @25℃ [A]	$R_{DS(on),max}$ @25℃ [Ω]	$V_{GS(th),typ}$ [V]	Polarity	Package	Feature/Status
600	TSAN078R60	48	0.078	3.5	N	TO-3PN	
	TSAN080R60S	46	0.080	3.0	N		Fast Recovery Type
650	TSAN080R65AS*	46	0.080	4.0	N		Fast Recovery Type
	TSAN041R65AS*	76	0.041	4.0	N		Fast Recovery Type

* Under Development

Package Information

Discrete

TYPE		D-PAK / I-PAK	TO-220	TO-220F	TO-3PN	TO-3PF	TO-247	TO-264
Dimension (mm)	W	6.60	9.90	10.16	15.60	15.50	15.94	20.00
	L	9.50 / 16.10	28.78	28.85	39.90	43.80	41.26	46.00
	T	2.30	4.50	4.70	4.80	5.50	5.02	5.00

Module

TYPE		34mm	62mm	EconoPower3
Dimension (mm)	W	94.00	107.60	152.00
	L	31.70	62.60	62.00
	T	29.00	29.00	20.80

Power Integration Module

TYPE		EasyPower2
Dimension (mm)	W	56.70
	L	48.00
	T	12.00

Certification

ISO / TS 16949

ISO / TS16949
SAI GLOBAL, 2017.

ISO 14001

ISO14001
ISC GLOBAL, 2015.

Small Giant Company of korea

Small Giant Company of korea
Minister of Small and Medium, 2017.

Adcanced Technology Center

Adcanced Technology Center(ATC)
Ministry of Trade, 2017.